

50 V low VCEsat PNP transistor

Manufacturers	NXP Semiconductor
Package/Case	SOT223
Product Type	Transistors
RoHS	
Lifecycle	



Images are for reference only

Please submit RFQ for PBSS5350Z or [Email to us: sales@ovaga.com](mailto:sales@ovaga.com) We will contact you in 12 hours.

[RFQ](#)

General Description

PBSS5350Z is a PNP Bipolar Junction Transistor (BJT) designed for low voltage, high speed switching applications. It is manufactured by NXP Semiconductors and has the following features:

Features

Collector-emitter voltage: -50 V

Collector current: -1 A

Low collector-emitter saturation voltage: 300 mV

High current gain: hFE > 100

Application

DC-DC converters

Voltage regulators

Load switches

Power management in portable devices

Battery-powered equipment



Related Products



[PBSS4350Z](#)

NXP Semiconductor
SOT-223



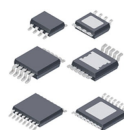
[PMPB27EP](#)

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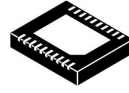
[PBSS4041SPN](#)

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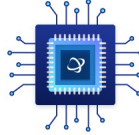
[PMDPB30XN](#)

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